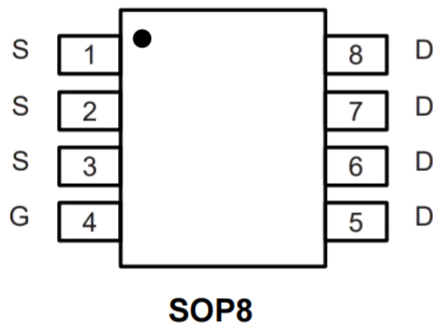


Product Summary

- V_{DS} 100 V
- I_{DS} (@ $V_{GS} = 10V$) 8A
- $R_{DS(ON)}$ (@ $V_{GS} = 10V$) $\leq 24m\Omega$

Reference:SI4486EY-T1-E3

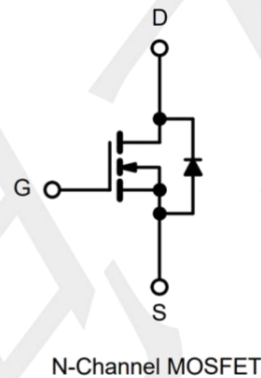
Package and Pin Configuration



Application

- LED Backlighting
- Synchronous Rectifiers for SMPS
- Power management
- PWM Application

Circuit diagram



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	8	A
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	32	A
Single Pulse Avalanche Energy	EAS	80	mJ
Maximum Power Dissipation, $T_A = 25^\circ C$	P_D	3.5	W
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ C$

Thermal Characteristic

PARAMETER	Symbol	Value	Unit
Thermal Resistance Junction-ambient	$R_{\theta JA}$	70	$^\circ C/W$
Thermal Resistance Junction-Case	$R_{\theta JC}$	36	$^\circ C/W$

notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. When mounted on 1" square PCB (FR4 material).

Electrical Characteristics (T_A=25°C unless otherwise noted)

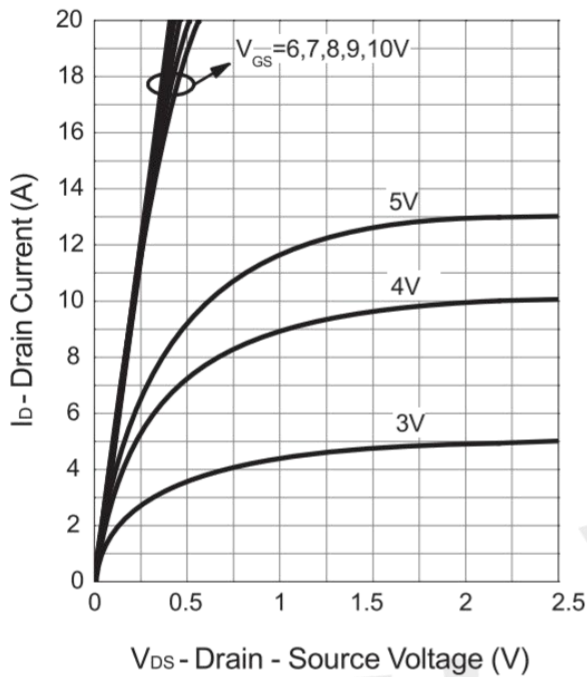
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	BV _{DSS}	100	--	--	V
Gate-Source Threshold Voltage	V _{DS} =V _{GS} , I _D = 250μA	V _{GS(th)}	1.0	2.0	3.0	V
Gate-Source Leakage	V _{DS} =0V, V _{GS} = ±20V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} =0V	I _{DSS}	--	--	1	μA
	V _{DS} = 100V, T _J =85°C		--	--	30	μA
Drain-Source On-State Resistance (Note 1)	V _{GS} = 10V, I _D =8A	R _{DS(on)}	--	20	24	mΩ
	V _{GS} = 4.5V, I _D =6A		--	24	32	
Forward Transconductance (Note 2)	V _{DS} = 5V, I _D = 3A	g _{fs}	--	25	--	S
Dynamic (Note 2)						
Total Gate Charge (Note 3)	V _{DS} = 80V, I _D =8A, V _{GS} =10V	Q _g	--	78	--	nC
Gate-Source Charge (Note 3)		Q _{gs}	--	8.0	--	
Gate-Drain Charge (Note 3)		Q _{gd}	--	15	--	
Input Capacitance	V _{DS} =25V, V _{GS} = 0V, F= 1.0MHz	C _{iss}	--	3400	--	pF
Output Capacitance		C _{oss}	--	110	--	
Reverse Transfer Capacitance		C _{rss}	--	90	--	
Switching						
Turn-On Delay Time (Note 3)	V _{DD} = 50V, I _D = 8A, V _{GS} = 10V, R _G = 6Ω.	t _{d(on)}	--	20	--	nS
Rise Time (Note 3)		t _r	--	14	--	
Turn-Off Delay Time (Note 3)		t _{d(off)}	--	44	--	
Fall Time (Note 3)		t _f	--	12	--	
Source-Drain Diode Ratings and Characteristics (Note 2)						
Forward Voltage	V _{GS} = 0V, I _{SD} = 4A	V _{SD}	--	0.8	1.3	V
Continuous Source Current	Integral reverse diode in the MOSFET	I _S	--	--	8	A
Pulsed Current (Note 1)		I _{SM}	--	--	32	A

Notes:

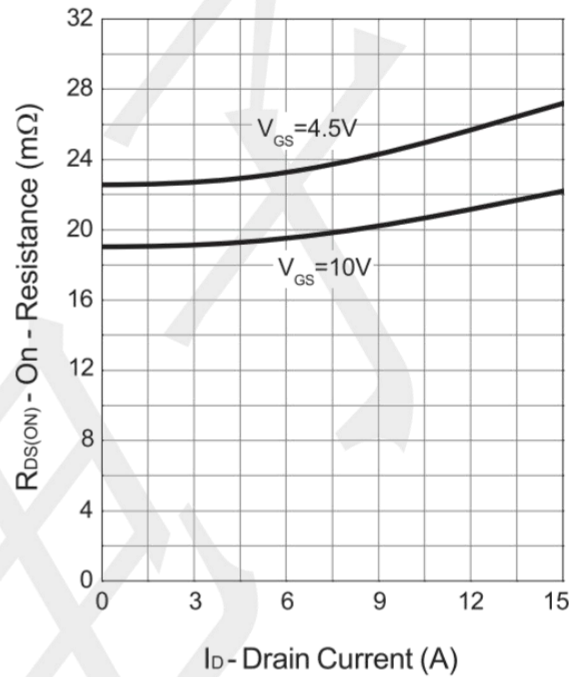
1. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
2. Guaranteed by design, not subject to production testing.
3. Independent of operating temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

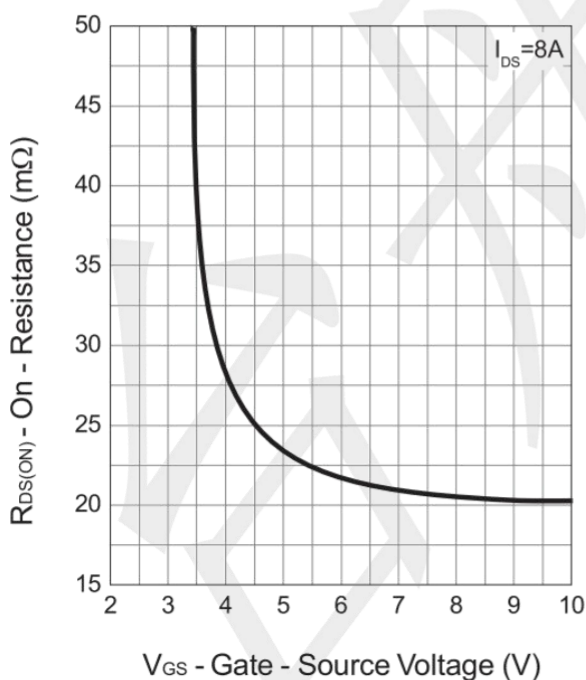
Output Characteristics



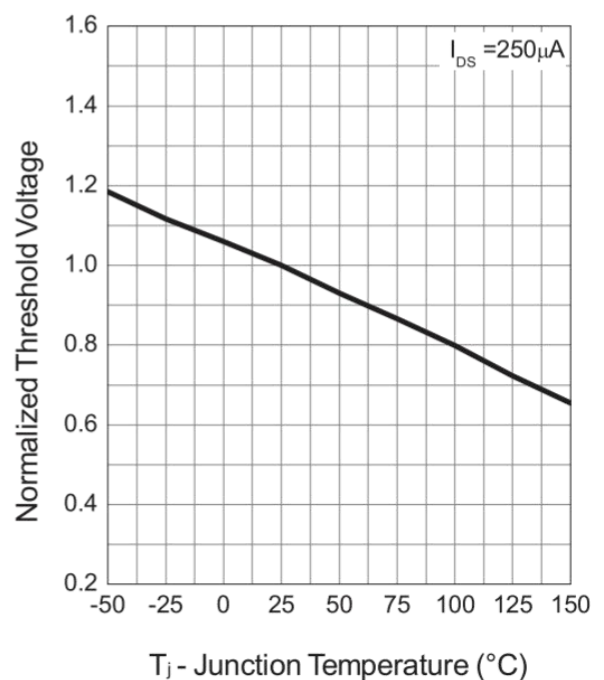
Drain-Source On Resistance



Gate-Source On Resistance

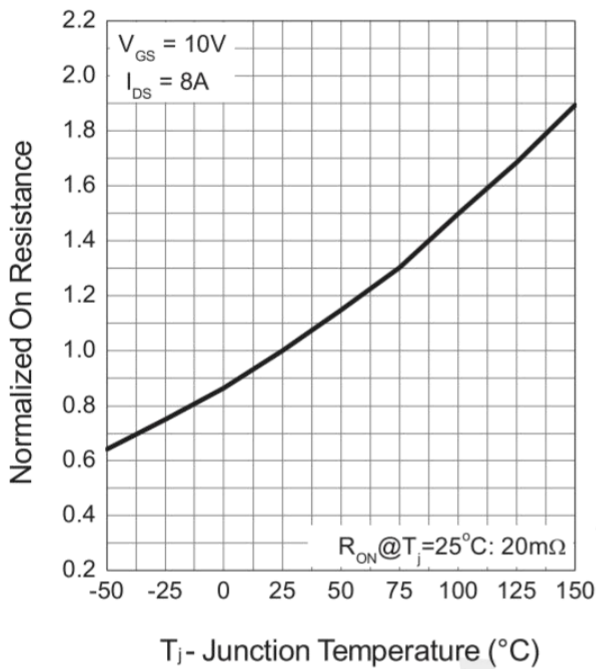


Gate Threshold Voltage

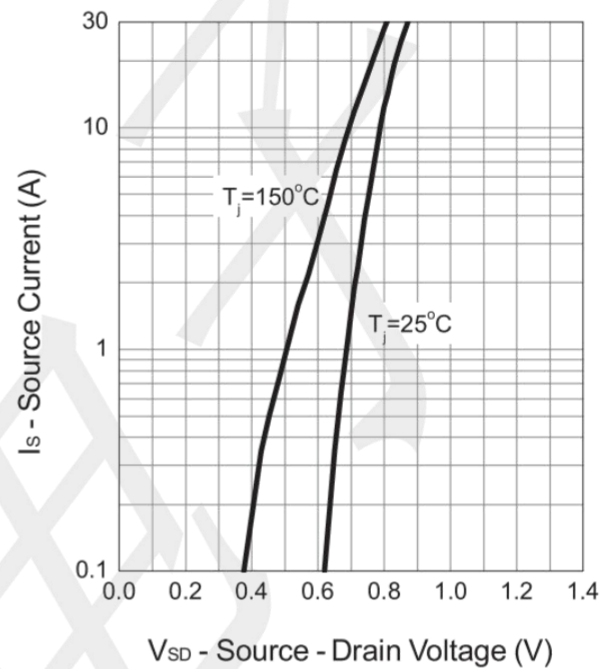


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

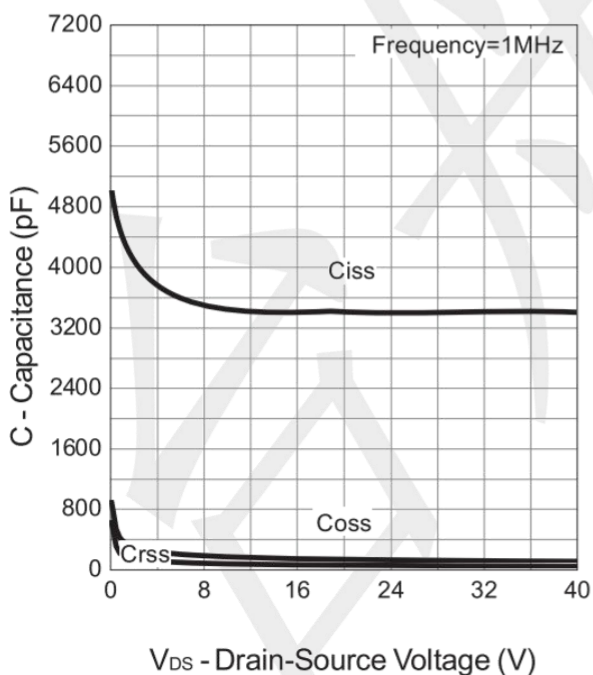
Drain-Source On Resistance



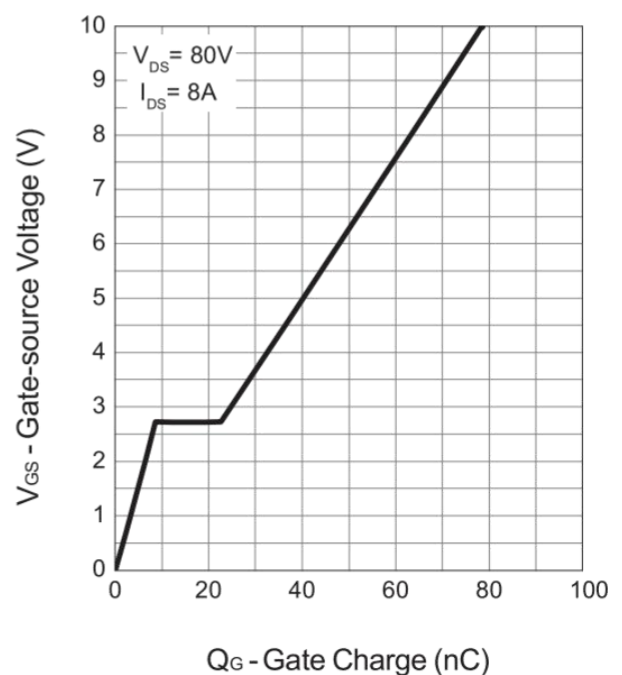
Source-Drain Diode Forward



Capacitance

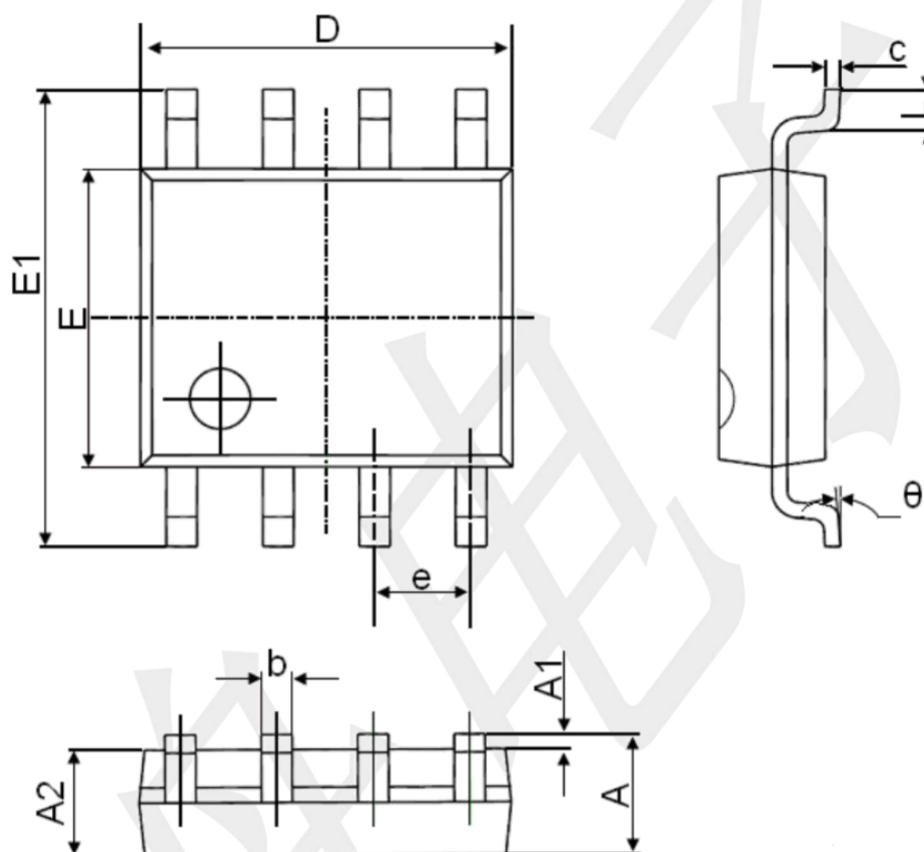


Gate Charge



Package Information

SOP8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°